N-Channel JFET Low-Frequency Low-Noise Amplifier

BSR57

Total Power Dissipation

Junction Temperature

Storage Temperature Range

Up to $T_{amb} = 40^{\circ}\dot{C}$

• This device is designed for low-power chopper or switching application sourced from process 51

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Parameter	Symbol	Value	Unit
Drain Gate Voltage	V _{DGO}	40	V
Gate Source Voltage	V _{GSO}	40	V
Forward Gate Current	I _{GF}	50	mA

 P_{tot}

T_{STG}

ТJ

250

55 to +150

150

mW

°C

°C

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the
device. If any of these limits are exceeded, device functionality should not be
assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol Param	eter Test Condition	Min.	Тур.
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